

General Purpose Transistor

NPN Silicon

MMBT3904L, SMMBT3904L

Features

- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable



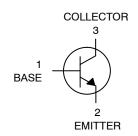
Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V _{CEO}	40	Vdc
Collector - Base Voltage	V _{CBO}	60	Vdc
Emitter - Base Voltage	V _{EBO}	6.0	Vdc
Collector Current - Continuous	I _C	200	mAdc
Collector Current - Peak (Note 3)	I _{CM}	900	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) @T _A = 25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) @T _A = 25°C Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.
- 3. Reference SOA curve.





SOT-23 (TO-236) CASE 318 STYLE 6

MARKING DIAGRAM



1AM = Specific Device Code

M = Date Code*■ Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBT3904LT1G	SOT-23	3000 / Tape &
SMMBT3904LT1G	(Pb-Free)	Reel
MMBT3904LT3G	SOT-23	10,000 / Tape &
SMMBT3904LT3G	(Pb-Free)	Reel

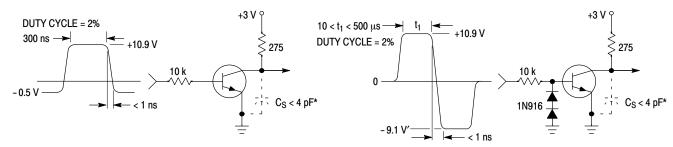
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Chara	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS					
Collector - Emitter Breakdown Voltage (Id	V _{(BR)CEO}	40	-	Vdc	
Collector - Base Breakdown Voltage (I _C	= 10 μAdc, I _E = 0)	V _{(BR)CBO}	60	-	Vdc
Emitter – Base Breakdown Voltage (I _E =	10 μAdc, I _C = 0)	V _{(BR)EBO}	6.0	_	Vdc
Base Cutoff Current ($V_{CE} = 30 \text{ Vdc}$, V_{EB}	= 3.0 Vdc)	I _{BL}	-	50	nAdc
Collector Cutoff Current (V _{CE} = 30 Vdc, V	V _{EB} = 3.0 Vdc)	I _{CEX}	-	50	nAdc
ON CHARACTERISTICS (Note 4)					
$\begin{array}{l} \text{DC Current Gain} \\ \text{(I}_{C} = 0.1 \text{ mAdc, V}_{CE} = 1.0 \text{ Vdc)} \\ \text{(I}_{C} = 1.0 \text{ mAdc, V}_{CE} = 1.0 \text{ Vdc)} \\ \text{(I}_{C} = 10 \text{ mAdc, V}_{CE} = 1.0 \text{ Vdc)} \\ \text{(I}_{C} = 10 \text{ mAdc, V}_{CE} = 1.0 \text{ Vdc)} \\ \text{(I}_{C} = 50 \text{ mAdc, V}_{CE} = 1.0 \text{ Vdc)} \\ \text{(I}_{C} = 100 \text{ mAdc, V}_{CE} = 1.0 \text{ Vdc)} \end{array}$	H _{FE}	40 70 100 60 30	- 300 - -	-	
	V _{CE(sat)}	- -	0.2 0.3	Vdc	
$ \begin{array}{l} \text{Base-Emitter Saturation Voltage} \\ \text{(I}_{C} = \text{10 mAdc, I}_{B} = \text{1.0 mAdc)} \\ \text{(I}_{C} = \text{50 mAdc, I}_{B} = \text{5.0 mAdc)} \end{array} $	V _{BE(sat)}	0.65	0.85 0.95	Vdc	
SMALL-SIGNAL CHARACTERISTICS		•			
Current - Gain - Bandwidth Product (I _C =	= 10 mAdc, V _{CE} = 20 Vdc, f = 100 MHz)	f _T	300	-	MHz
Output Capacitance (V _{CB} = 5.0 Vdc, I _E =	0, f = 1.0 MHz)	C _{obo}	-	4.0	pF
Input Capacitance (V _{EB} = 0.5 Vdc, I _C = 0), f = 1.0 MHz)	C _{ibo}	-	8.0	pF
Input Impedance ($V_{CE} = 10 \text{ Vdc}$, $I_{C} = 1.0 \text{ Vdc}$) mAdc, f = 1.0 kHz)	h _{ie}	1.0	10	kΩ
Voltage Feedback Ratio ($V_{CE} = 10 \text{ Vdc}$,	I _C = 1.0 mAdc, f = 1.0 kHz)	h _{re}	0.5	8.0	X 10 ⁻⁴
Small – Signal Current Gain (V _{CE} = 10 V	dc, I _C = 1.0 mAdc, f = 1.0 kHz)	h _{fe}	100	400	-
Output Admittance ($V_{CE} = 10 \text{ Vdc}, I_{C} = 1$.0 mAdc, f = 1.0 kHz)	h _{oe}	1.0	40	μmhos
Noise Figure ($V_{CE} = 5.0 \text{ Vdc}$, $I_{C} = 100 \mu$	NF	-	5.0	dB	
SWITCHING CHARACTERISTICS					
Delay Time	(V _{CC} = 3.0 Vdc, V _{BE} = -0.5 Vdc,	t _d	-	35	no
Rise Time	$I_C = 10 \text{ mAdc}, I_{B1} = 1.0 \text{ mAdc})$	t _r	-	35	ns
Storage Time	(V _{CC} = 3.0 Vdc,	t _s	-	200	
Fall Time	$I_C = 10 \text{ mAdc}, I_{B1} = I_{B2} = 1.0 \text{ mAdc}$	t _f	_	50	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

^{4.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

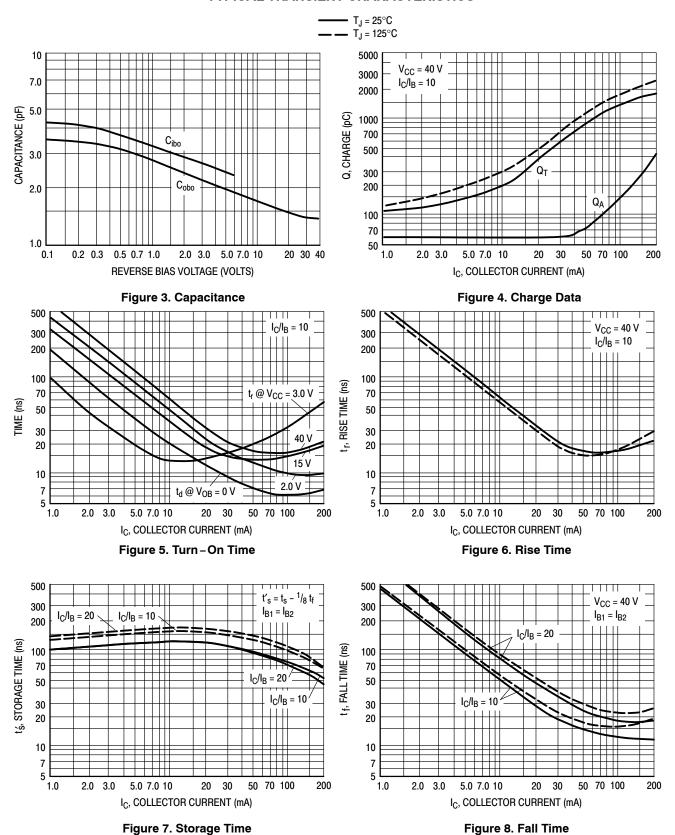


^{*} Total shunt capacitance of test jig and connectors

Figure 1. Delay and Rise Time Equivalent Test Circuit

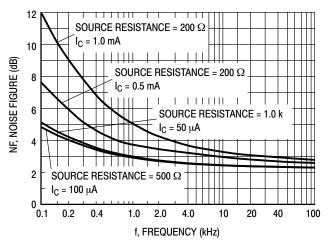
Figure 2. Storage and Fall Time Equivalent Test Circuit

TYPICAL TRANSIENT CHARACTERISTICS



TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE VARIATIONS

 $(V_{CE} = 5.0 \text{ Vdc}, T_A = 25^{\circ}\text{C}, Bandwidth = 1.0 \text{ Hz})$



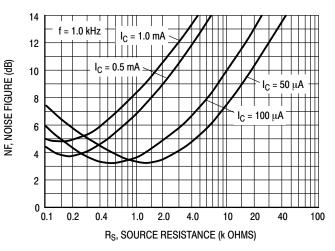
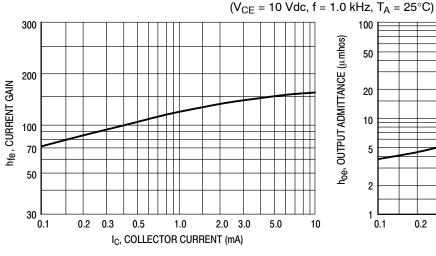


Figure 9.

Figure 10.

h PARAMETERS



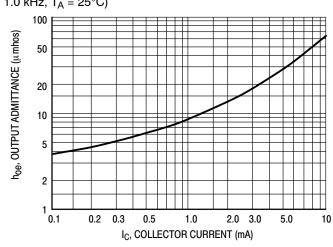
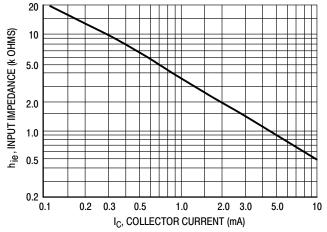
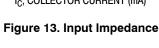


Figure 11. Current Gain







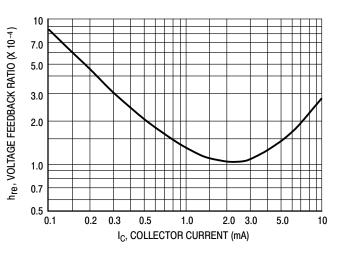


Figure 14. Voltage Feedback Ratio

TYPICAL STATIC CHARACTERISTICS

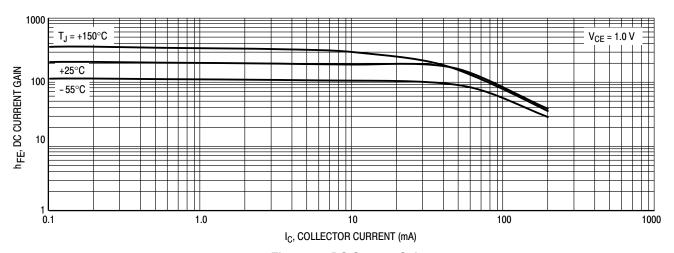


Figure 15. DC Current Gain

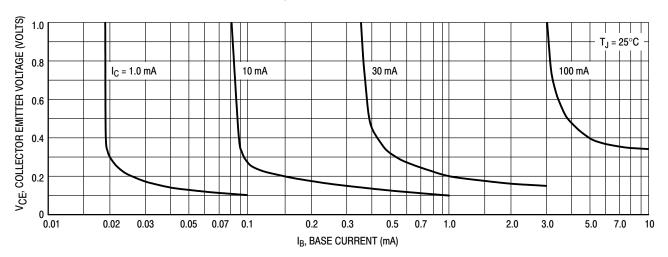


Figure 16. Collector Saturation Region

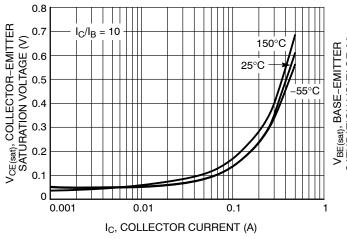


Figure 17. Collector Emitter Saturation Voltage vs. Collector Current

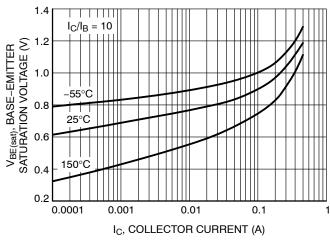


Figure 18. Base Emitter Saturation Voltage vs.
Collector Current

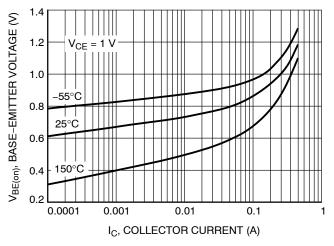


Figure 19. Base Emitter Voltage vs. Collector Current

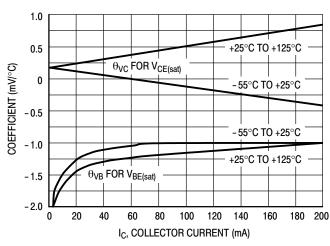


Figure 20. Temperature Coefficients

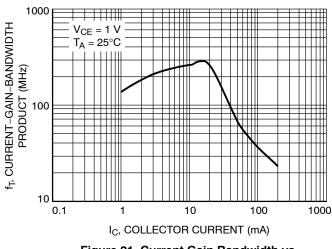


Figure 21. Current Gain Bandwidth vs. Collector Current

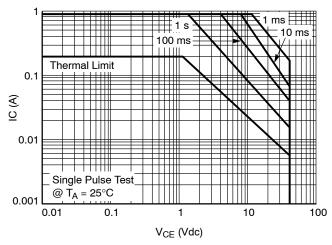


Figure 22. Safe Operating Area

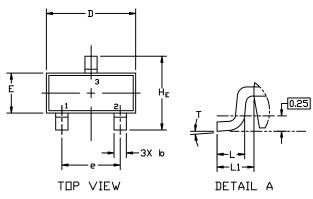




SOT-23 (TO-236) CASE 318 ISSUE AT

DATE 01 MAR 2023









NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS		INCHES			
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
Ε	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0*		10°	0*		10°

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

M = Date Code

■ = Pb-Free Package



RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

STYLES ON PAGE 2

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^{*}This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



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DATE 01 MAR 2023

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	1	
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE	STYLE 19: N PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE	STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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